

# Silicon Carbide (SiC) MOSFET – 33 mohm, 650 V, M2, TO-247-4L

## NTH4L045N065SC1

### Features

- Typ.  $R_{DS(on)} = 33\text{ m}\Omega @ V_{GS} = 18\text{ V}$   
Typ.  $R_{DS(on)} = 45\text{ m}\Omega @ V_{GS} = 15\text{ V}$
- Ultra Low Gate Charge ( $Q_{G(tot)} = 105\text{ nC}$ )
- High Speed Switching with Low Capacitance ( $C_{oss} = 162\text{ pF}$ )
- 100% Avalanche Tested
- $T_J = 175^\circ\text{C}$
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

### Typical Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Powere Supplies)
- Energy Storages

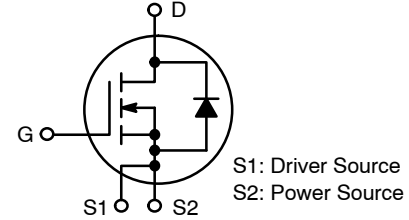
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DSS}$	650	V
Gate-to-Source Voltage		$V_{GS}$	-8/+22	V
Recommended Operation Values of Gate-to-Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+18	V
Continuous Drain Current (Note 1)	Steady State $T_C = 25^\circ\text{C}$	$I_D$	55	A
Power Dissipation (Note 1)		$P_D$	187	W
Continuous Drain Current (Note 1)	Steady State $T_C = 100^\circ\text{C}$	$I_D$	39	A
Power Dissipation (Note 1)		$P_D$	94	W
Pulsed Drain Current (Note 2)	$T_C = 25^\circ\text{C}$	$I_{DM}$	197	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)		$I_S$	45	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 12\text{ A}, L = 1\text{ mH}$ ) (Note 3)		$E_{AS}$	72	mJ
Maximum Lead Temperature for Soldering (1/8" from case for 5 s)		$T_L$	300	$^\circ\text{C}$

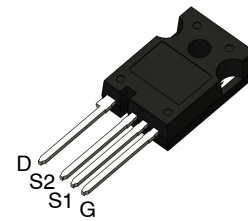
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. EAS of 72 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1\text{ mH}$ ,  $I_{AS} = 12\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $V_{GS} = 18\text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	50 m $\Omega$ @ 18 V	55 A



N-CHANNEL MOSFET



TO247-4L  
CASE 340CJ

### MARKING DIAGRAM



H4L045065SC1 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

Device	Package	Shipping
NTH4L045N065SC1	TO247-4L	30 Units / Tube

# NTH4L045N065SC1

## THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	0.8	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650	-	-	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 20\text{ mA}$ , referenced to $25^\circ\text{C}$	-	0.15	-	V/°C	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}$	$T_J = 25^\circ\text{C}$	-	-	10	$\mu\text{A}$
			$T_J = 175^\circ\text{C}$	-	-	1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +22/-8\text{ V}, V_{DS} = 0\text{ V}$	-	-	250	nA	

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 8\text{ mA}$	1.8	2.8	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5	-	+18	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 15\text{ V}, I_D = 25\text{ A}, T_J = 25^\circ\text{C}$	-	45	-	m $\Omega$
		$V_{GS} = 18\text{ V}, I_D = 25\text{ A}, T_J = 25^\circ\text{C}$	-	33	50	
		$V_{GS} = 18\text{ V}, I_D = 25\text{ A}, T_J = 175^\circ\text{C}$	-	41	-	
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	-	16	-	S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 325\text{ V}$	-	1870	-	pF
Output Capacitance	$C_{OSS}$		-	162	-	
Reverse Transfer Capacitance	$C_{RSS}$		-	14	-	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 520\text{ V}, I_D = 25\text{ A}$	-	105	-	nC
Gate-to-Source Charge	$Q_{GS}$		-	27	-	
Gate-to-Drain Charge	$Q_{GD}$		-	30	-	
Gate-Resistance	$R_G$	$f = 1\text{ MHz}$	-	3.1	-	$\Omega$

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 400\text{ V}, I_D = 25\text{ A}, R_G = 2.2\text{ }\Omega$ inductive load	-	13	-	ns
Rise Time	$t_r$		-	14	-	
Turn-Off Delay Time	$t_{d(OFF)}$		-	26	-	
Fall Time	$t_f$		-	7	-	
Turn-On Switching Loss	$E_{ON}$		-	47	-	$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$		-	33	-	
Total Switching Loss	$E_{tot}$		-	80	-	

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$	-	-	45	A
Pulsed Source-Drain Diode Forward Current (Note 2)	$I_{SDM}$		-	-	197	
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}, T_J = 25^\circ\text{C}$	-	4.4	-	V

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>SOURCE-DRAIN DIODE CHARACTERISTICS</b>						
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/18\text{ V}$ , $I_{SD} = 25\text{ A}$ , $di_S/dt = 1000\text{ A}/\mu\text{s}$	-	20	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	108	-	nC
Reverse Recovery Energy	$E_{REC}$		-	4.5	-	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$		-	11	-	A
Charge Time	$T_a$		-	11	-	ns
Discharge Time	$T_b$		-	8.5	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

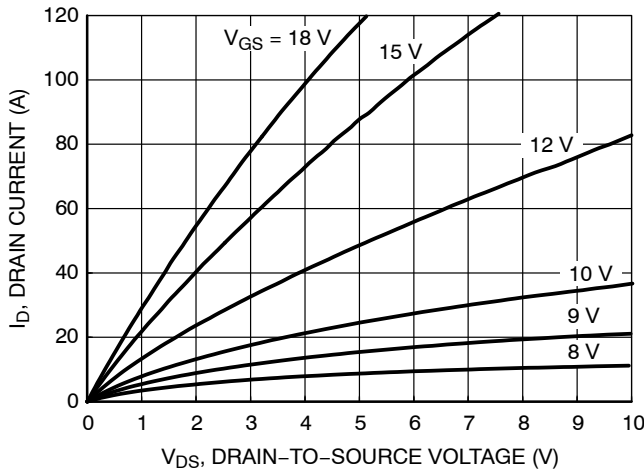


Figure 1. On-Region Characteristics

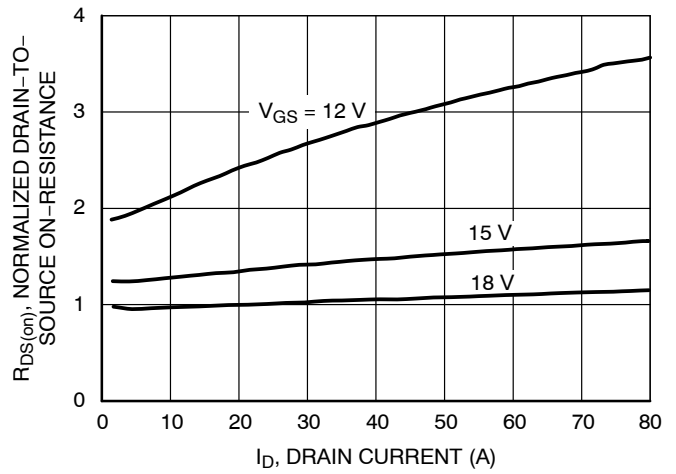


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

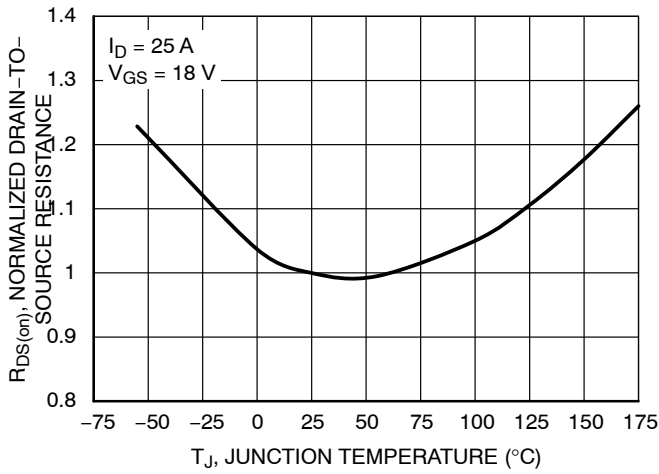


Figure 3. On-Resistance Variation with Temperature

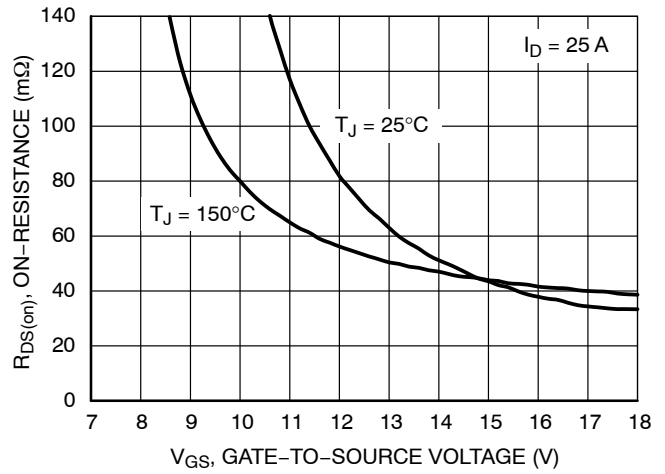


Figure 4. On-Resistance vs. Gate-to-Source Voltage

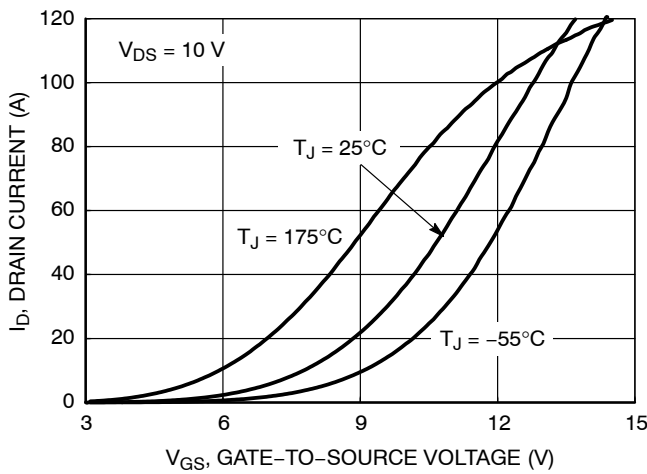


Figure 5. Transfer Characteristics

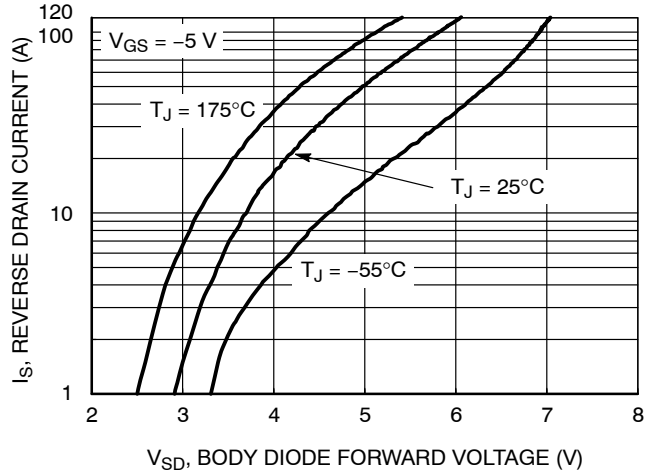


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS (continued)

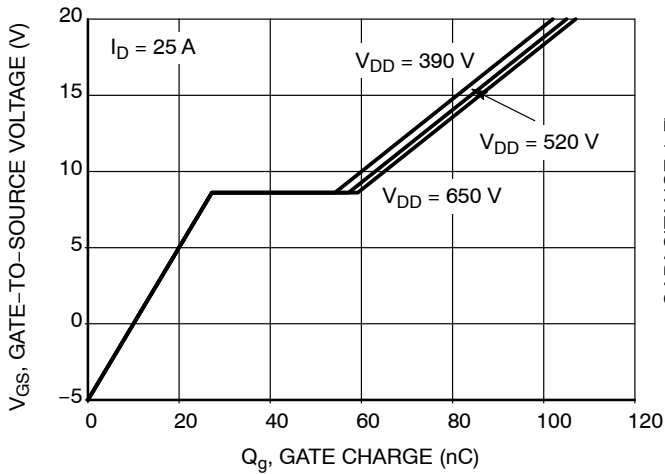


Figure 7. Gate-to-Source Voltage vs. Total Charge

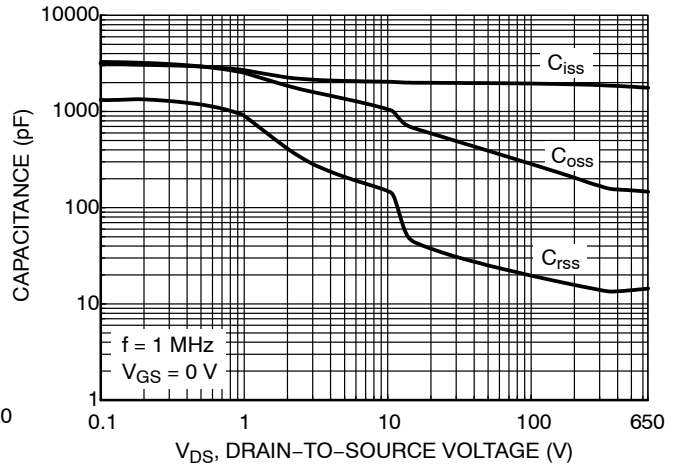


Figure 8. Capacitance vs. Drain-to-Source Voltage

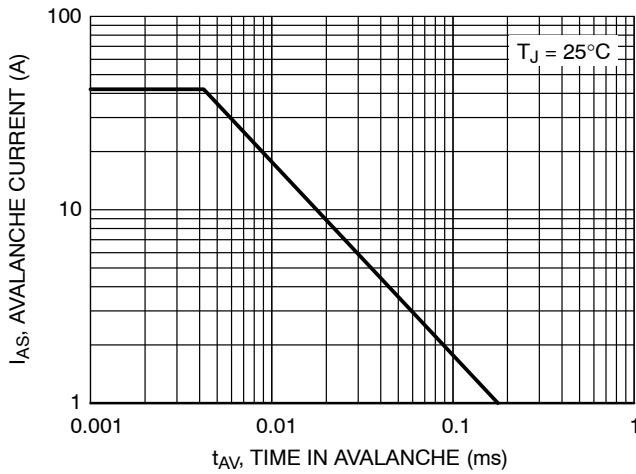


Figure 9. Unclamped Inductive Switching Capability

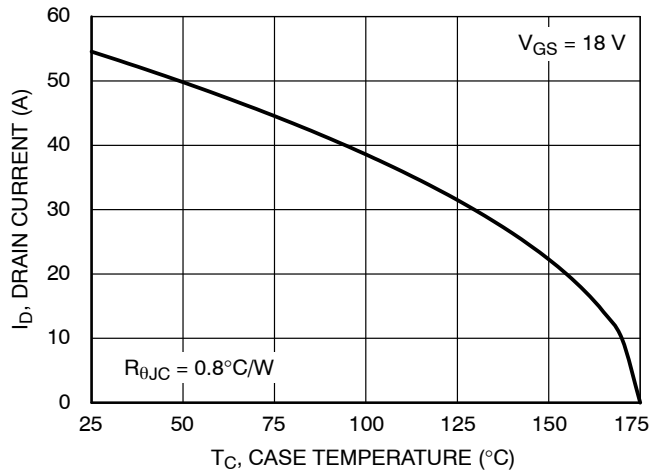


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

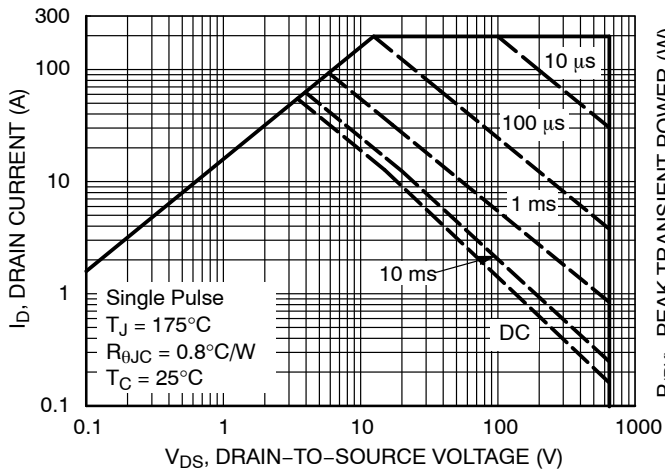


Figure 11. Safe Operating Area

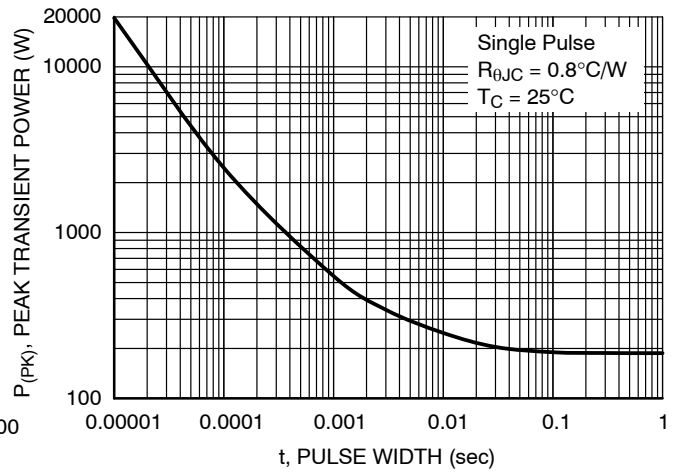


Figure 12. Single Pulse Maximum Power Dissipation

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## TYPICAL CHARACTERISTICS (continued)

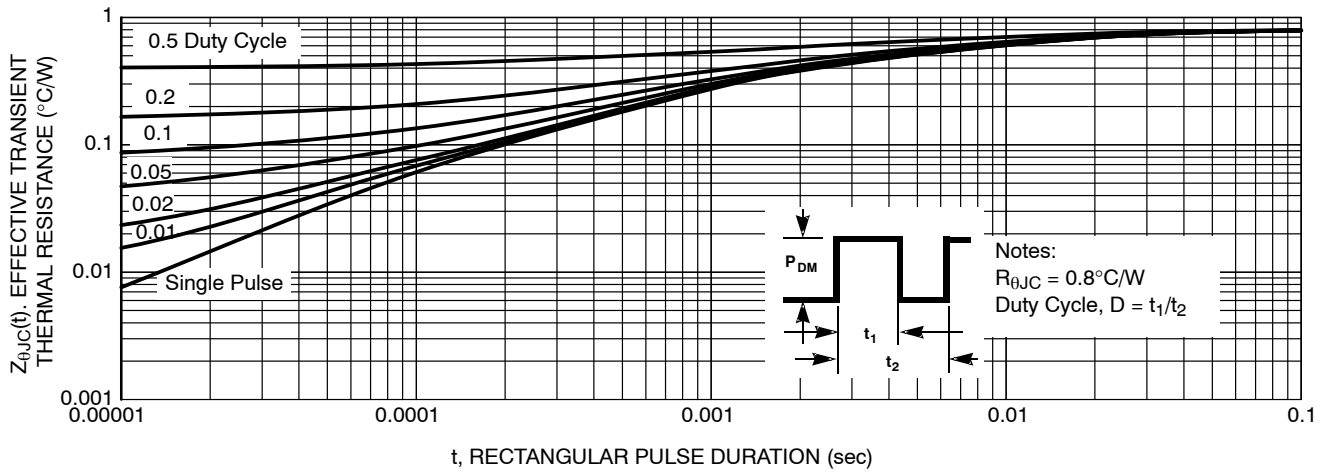


Figure 13. Junction-to-Case Thermal Response

# MECHANICAL CASE OUTLINE

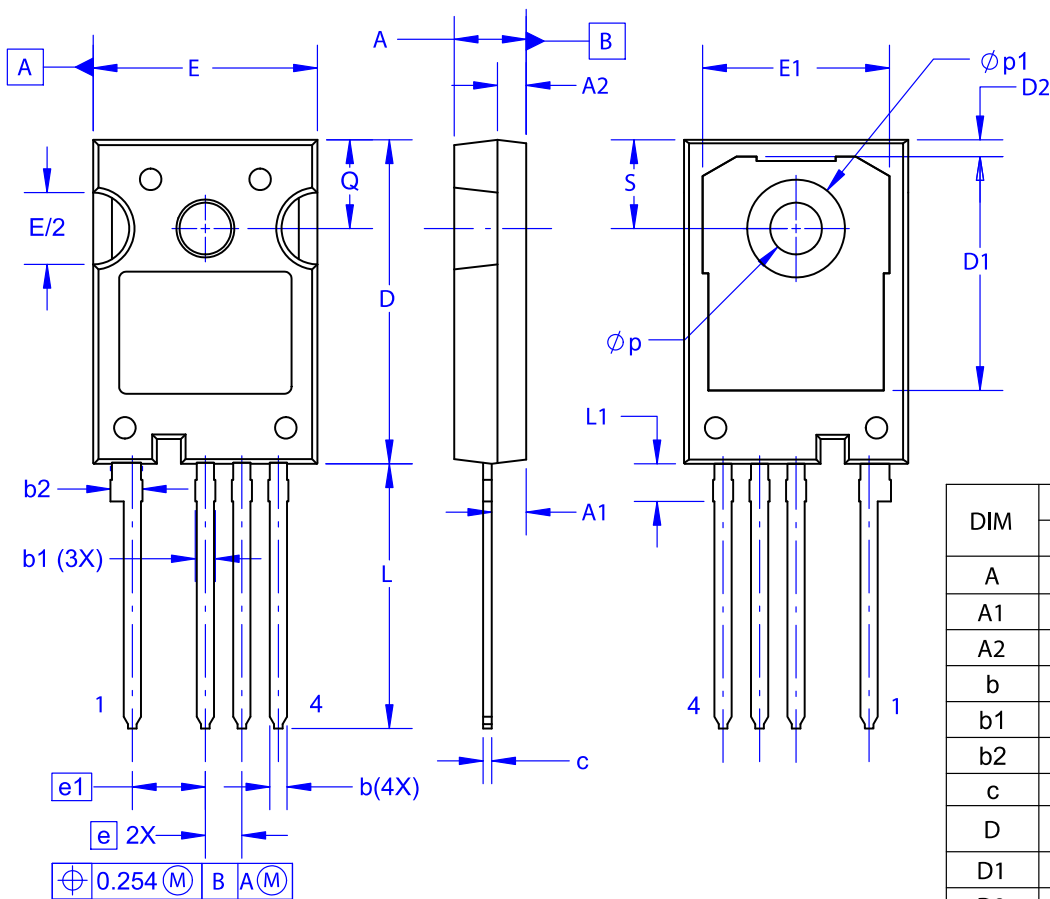
## PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD  
CASE 340CJ  
ISSUE A

DATE 16 SEP 2019



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

**NOTES:**

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
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